

NTS2101P

MOSFET – Power, Single, P-Channel, SC-70

-8.0 V, -1.4 A



ON Semiconductor®

<http://onsemi.com>

Features

- Leading Trench Technology for Low $R_{DS(on)}$ Extending Battery Life
- -1.8 V Rated for Low Voltage Gate Drive
- SC-70 Surface Mount for Small Footprint (2 x 2 mm)
- Pb-Free Package is Available

Applications

- High Side Load Switch
- Charging Circuit
- Single Cell Battery Applications such as Cell Phones, Digital Cameras, PDAs, etc.

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Units	
Drain-to-Source Voltage		V_{DSS}	-8.0	V	
Gate-to-Source Voltage		V_{GS}	± 8.0	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	-1.4	A
				$T_A = 70^\circ\text{C}$	-1.1
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	-1.5	A	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	0.29	W
	$t \leq 5$ s			0.33	W
Pulsed Drain Current	$tp = 10$ μs	I_{DM}	-3.0	A	
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode), Continuous		I_S	-0.46	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS

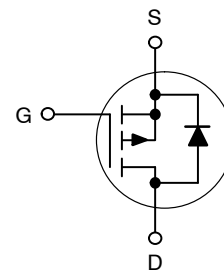
Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	430	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5$ s (Note 1)	$R_{\theta JA}$	375	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

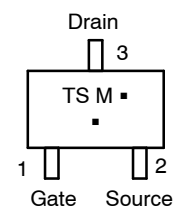
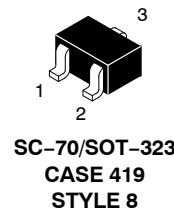
1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
-8.0 V	65 m Ω @ -4.5 V	-1.4 A
	78 m Ω @ -2.5 V	
	117 m Ω @ -1.8 V	

P-Channel MOSFET



MARKING DIAGRAM & PIN ASSIGNMENT



TS = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NTS2101PT1	SOT-323	3000/Tape & Reel
NTS2101PT1G	SOT-323 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTS2101P

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -250 μA	-8.0	-20		V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			-10		mV/°C	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = -6.4 V	T _J = 25°C			-1.0	μA
			T _J = 70°C				
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8.0 V				±100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250 μA	-0.45	-0.7		V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			2.6		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = -4.5 V, I _D = -1.0 A		65	100	mΩ
		V _{GS} = -2.5 V, I _D = -0.5 A		78	140	
		V _{GS} = -1.8 V, I _D = -0.3 A		117	210	

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = -8.0 V		640		pF
Output Capacitance	C _{OSS}			120		
Reverse Transfer Capacitance	C _{RSS}			82		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = -5.0 V, V _{DD} = -5.0 V, I _D = -1.0 A		6.4		nC
Threshold Gate Charge	Q _{G(TH)}			0.7		
Gate-to-Source Charge	Q _{GS}			1.0		
Gate-to-Drain Charge	Q _{GD}			1.5		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = -4.5 V, V _{DD} = -4.0 V, I _D = -1.0 A, R _G = 6.2 Ω		6.2		ns
Rise Time	t _r			15		
Turn-Off Delay Time	t _{d(OFF)}			26		
Fall Time	t _f			18		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = -0.3 A	T _J = 25°C		-0.62	-1.2	V
			T _J = 125°C		-0.51		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _{SD} /dt = 100 A/μs, I _S = -1.0 A		23.4		ns	
Charge Time	T _a			7.7			
Discharge Time	T _b			15.7			
Reverse Recovery Charge	Q _{RR}			9.5			nC

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

NTS2101P

TYPICAL ELECTRICAL CHARACTERISTICS

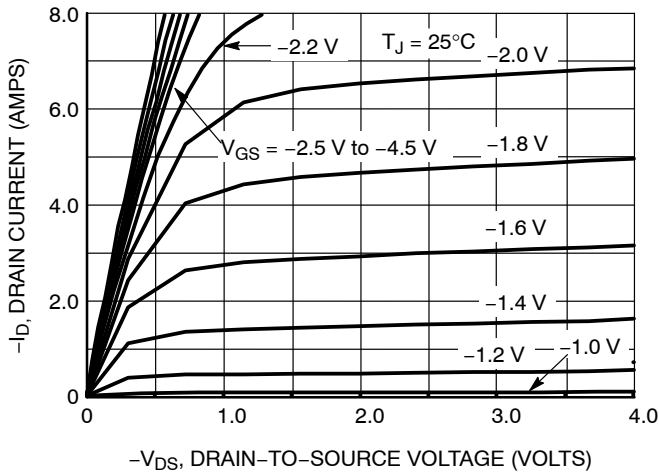


Figure 1. On-Region Characteristics

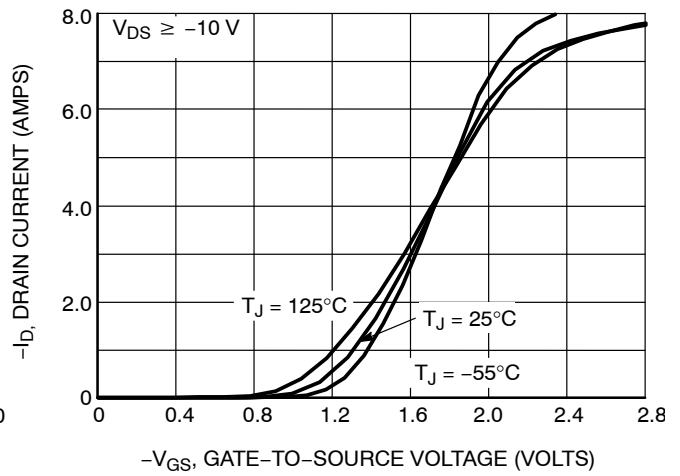


Figure 2. Transfer Characteristics

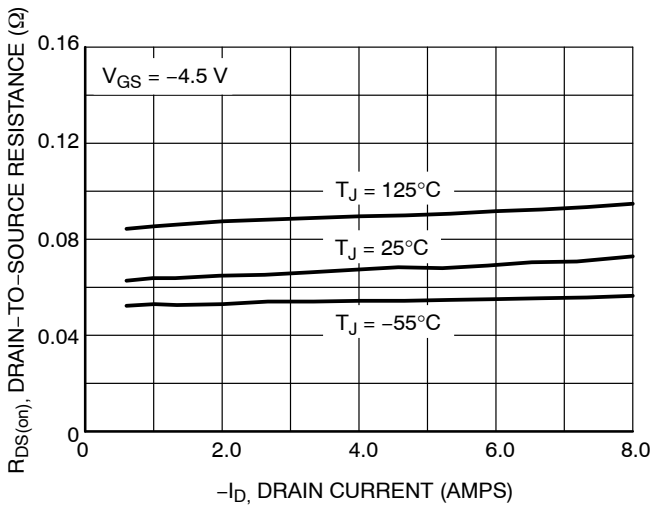


Figure 3. On-Resistance vs. Drain Current and Temperature

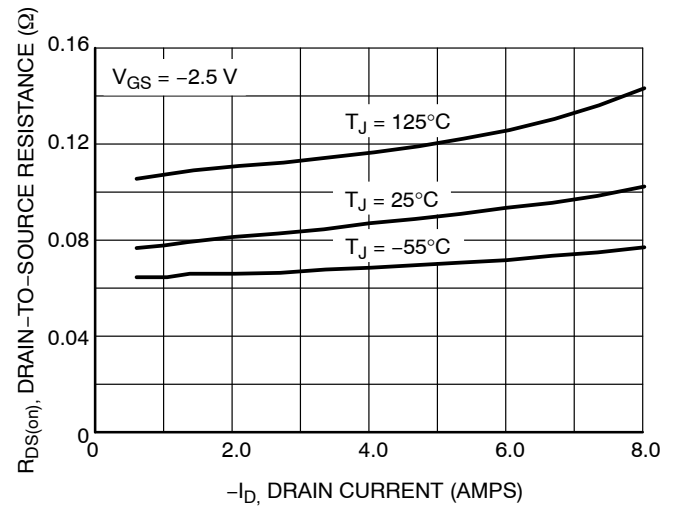


Figure 4. On-Resistance vs. Drain Current and Temperature

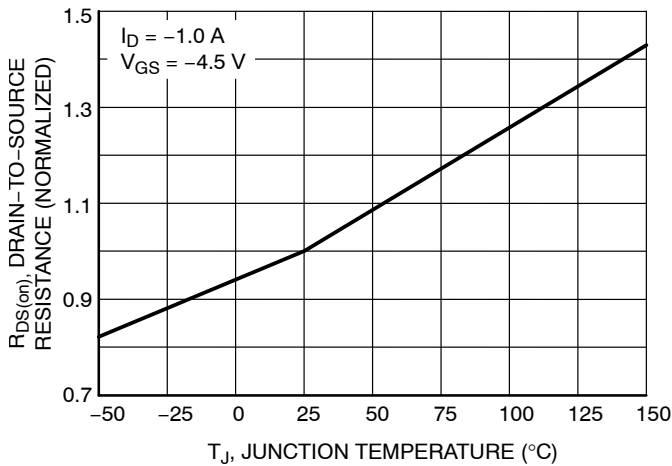


Figure 5. On-Resistance Variation with Temperature

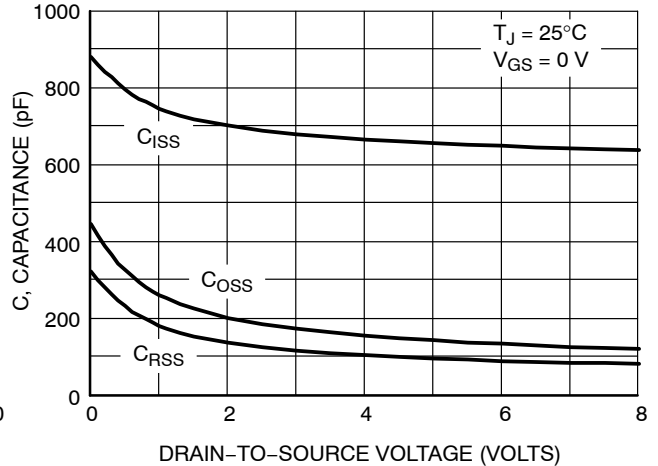


Figure 6. Capacitance Variation

NTS2101P

TYPICAL ELECTRICAL CHARACTERISTICS

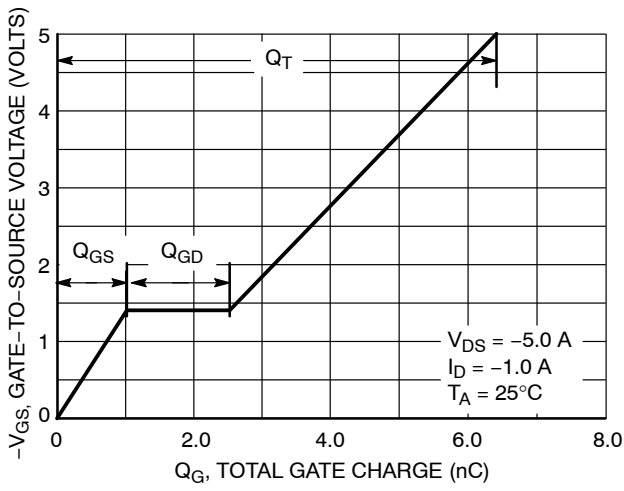


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Gate Charge

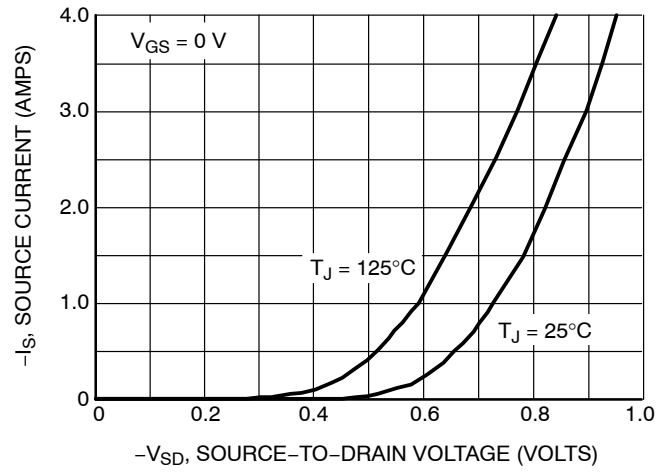


Figure 8. Diode Forward Voltage vs. Current

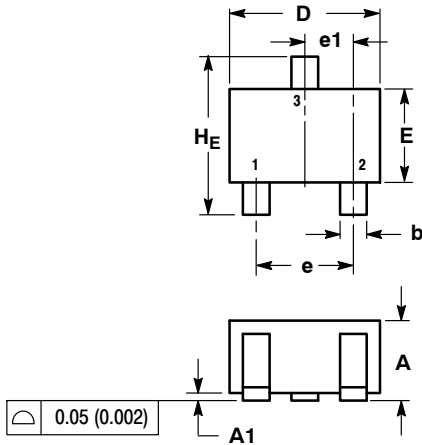
NTS2101P

PACKAGE DIMENSIONS

SC-70 (SOT-323)

CASE 419-04

ISSUE M



NOTES:

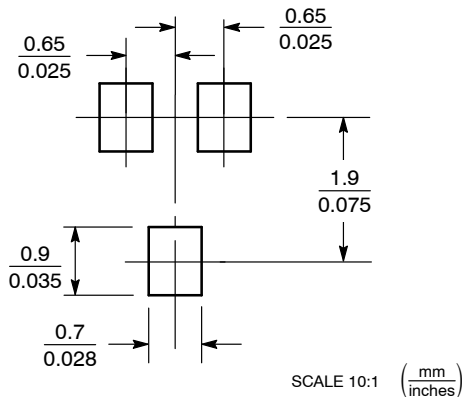
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 8:

1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA
Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada
Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your local Sales Representative.